

Power Management ICs for Automotive Body Control

Regulator with Voltage Detector and Watchdog Timer



BD3021HFP-M

No.10039EAT10

●Description

BD3021HFP-M is a regulator IC with integrated WDT (Watch Dog Timer), high output voltage accuracy $\pm 2.0\%$ and $80\mu\text{A}$ (Typ.) low circuit current consumption. BD3021HFP-M supports usage of low ESR ceramic capacitor for output stability. BD3021HFP-M can be a stable power supply for any applications while detecting malfunction of microcontrollers.

●Features

- 1) WDT Can be Switched ON/OFF by Using INH Pin
- 2) Low Circuit Current: $80\mu\text{A}$ (Typ.)
- 3) Output Circuit: Pch DMOS
- 4) High Output Voltage Accuracy: $5\text{V} \pm 2\%$
- 5) Supports Low ESR Ceramic Capacitor
- 6) Vcc Max Voltage: 50V
- 7) Integrated Over Current Protection and Thermal Shut Down
- 8) HRP7 packaging

●Applications

Any application using a microcontroller or a DSP such as automotive (body control), display, server, DVD, phone, etc...

●Absolute maximum ratings (Ta=25°C)

| Parameter | Symbol | Ratings | Unit |
|---------------------------------|--------|------------|------|
| Supply Voltage | Vcc | -0.3 ~ +50 | V |
| INH pin voltage | VINH | -0.3 ~ +15 | V |
| Regulator output pin voltage | VOUT | -0.3 ~ +15 | V |
| Reset output pin voltage | VRESET | -0.3 ~ +15 | V |
| Watchdog input pin voltage | VCLK | -0.3 ~ +15 | V |
| Reset delay setting pin voltage | VCT | -0.3 ~ +15 | V |
| Power dissipation | Pd | 1.6 | W |
| Operating temperature range | Topr | -40 ~ +125 | °C |
| Storage temperature range | Tstg | -55 ~ +150 | °C |
| Maximum junction temperature | Tjmax | 150 | °C |

*1 Not to exceed Pd.

*2 Reduced by $12.8\text{W} / ^\circ\text{C}$ over Ta = 25°C, when mounted on glass epoxy board: 70mm × 70mm × 1.6mm.

●Operating conditions (Ta=-40~125°C)

| Parameter | Symbol | Min | Max | Unit |
|----------------|--------|-----|------|------|
| Supply Voltage | Vcc | 5.6 | 36.0 | V |
| Output Current | Io | 0 | 500 | mA |

*3 For the output voltage, consider the voltage drop (dropout voltage) due to the output current.

NOTE: This product is not designed for protection against radioactive rays.

● **Electrical characteristics** (Unless otherwise specified, Ta=25°C, Vcc=13.5V, CLK=GND)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|---|----------|--------------|------|--------------|------|--|
| Overall Device | | | | | | |
| Bias current 1 | Icc1 | — | 80 | 130 | μA | Io=0mA |
| Bias current 2 | Icc2 | — | 150 | 300 | μA | Io=50mA(Ta=25°C) |
| Regulator | | | | | | |
| Output voltage | VOUT | 4.90 | 5.00 | 5.10 | V | Io=200mA |
| Line regulation | Line.Reg | — | 5 | 35 | mV | Vcc=5.6 ~ 36V |
| Load regulation | Load.Reg | — | 30 | 70 | mV | Io=5 ~ 200mA |
| Dropout voltage | ΔVd | — | 0.3 | 0.6 | V | Vcc=4.75V, Io=200mA |
| Ripple rejection | R.R. | 45 | 55 | — | dB | f=120Hz, ein=1Vrms, Io=100mA |
| Reset | | | | | | |
| Detection voltage | Vdet | 4.40 | 4.50 | 4.60 | V | |
| Hysteresis width | VHS | 50 | 100 | 150 | mV | |
| Output delay time Low→High (Power on reset time) | TdLH | 1.1 | 1.9 | 2.7 | ms | Vcc=Vdet±0.5V(Vcc=VOUT) INH=Open,CT=0.01μF |
| Output delay time High→Low | TdHL | — | 100 | 300 | μs | Vcc=Vdet±0.5V(Vcc=VOUT) INH= Open,CT=0.01μF |
| RESET discharge current | IRESET | 0.2 | — | — | mA | Vcc=1.5V,RESET=0.5V (Vcc=VOUT) |
| CT discharge current | Ict | 0.1 | — | — | mA | Vcc=1.5V,CT=0.5V (Vcc=VOUT) |
| Low output voltage | VRST | — | 0.1 | 0.2 | V | VOUT=4.0V |
| Min. operating voltage | VOPL | 1.5 | — | — | V | |
| Watchdog timer | | | | | | |
| CT switching threshold voltage High | VthH | 1.08 | 1.15 | 1.25 | V | WDT ON, INH= Open |
| CT switching threshold voltage Low | VthL | 0.13 | 0.15 | 0.17 | V | WDT ON, INH= Open |
| WDT Charge current | Ictc | 3.5 | 6.0 | 8.5 | μA | WDT ON, INH= Open, CT=0V |
| WDT Discharge current | Ictd | 1.2 | 2.0 | 2.8 | μA | WDT ON, INH= Open, CT=1.3V |
| Watchdog monitor time Low | TWH | 3.0 | 5.0 | 7.0 | ms | WDT ON, INH= Open, CT=0.01μF(Ceramic Cap) ※Characteristics of ceramic cap not considered. |
| Watchdog reset time | TWL | 1.0 | 1.7 | 2.4 | ms | |
| CLK Input pulse width | TWCLK | 500 | — | — | ns | |
| INH | | | | | | |
| WDT OFF threshold Voltage | VHINH | VOUT ×0.8 | — | VOUT | V | |
| WDT ON threshold voltage | VLINH | 0 | — | VOUT ×0.3 | V | |
| INH Input current | IINH | — | 10 | 20 | μA | INH=5V |

● **Electrical characteristics** (Unless otherwise specified, Ta=25°C, Vcc=13.5V, CLK=GND)

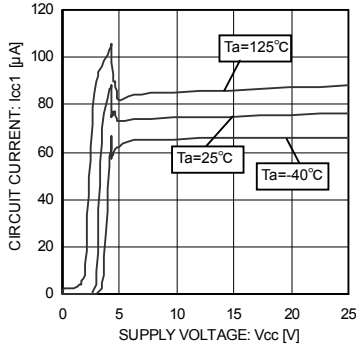


Fig.1 Circuit Current

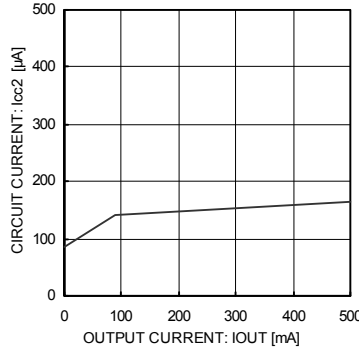


Fig.2 Circuit Current

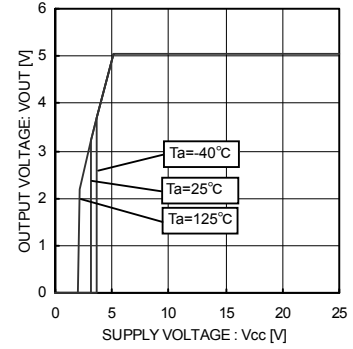


Fig.3 Input Stability

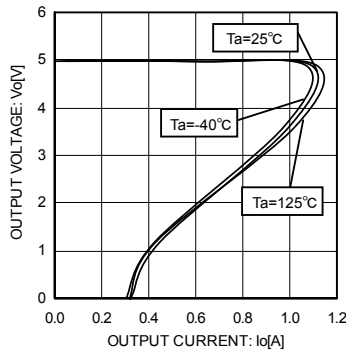


Fig. 4 Load Stability

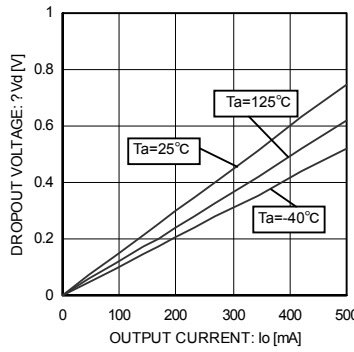


Fig.5 Dropout Voltage

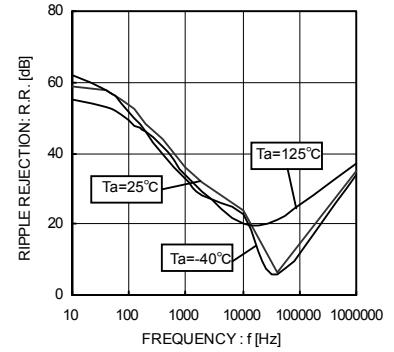


Fig. 6 Ripple Rejection

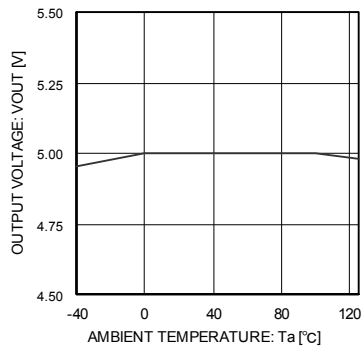


Fig. 7 Output Voltage Temperature Characteristics

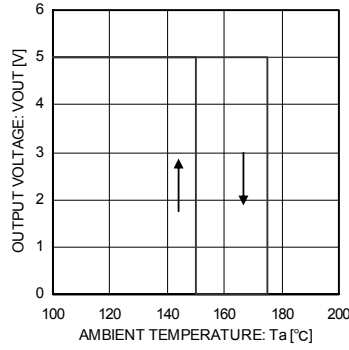


Fig.8 Thermal Shutdown Circuit Characteristics

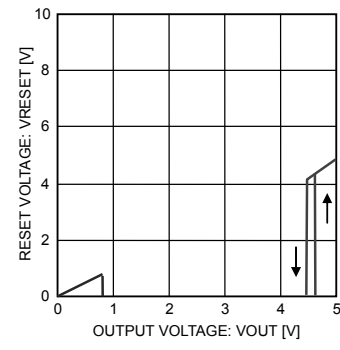


Fig.9 Restion Voltage (Vcc=VOUT)

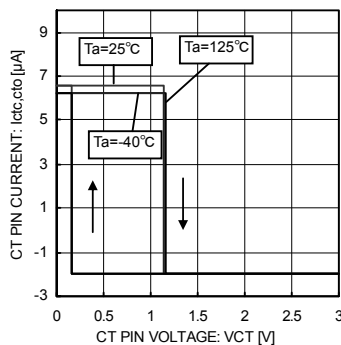


Fig.10 CT Pin Charge / Discharge Current (Vcc=5V)

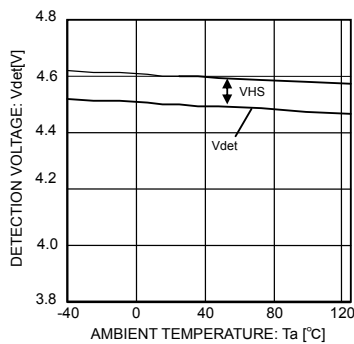


Fig.11 Reset Detection Voltage vs. Temperature

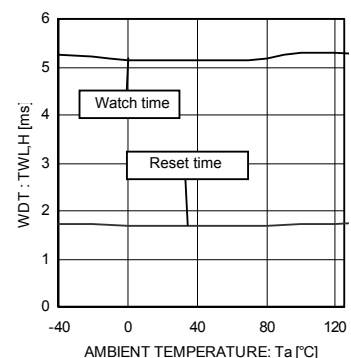
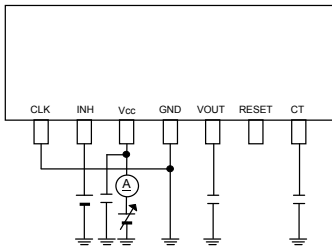
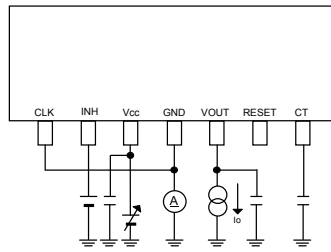


Fig.12 WDT Time vs. Temperature (CT=0.01µF)

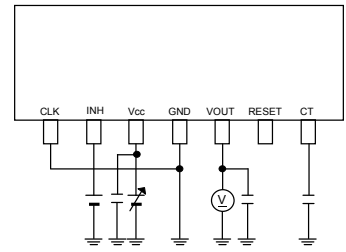
● Measurement Circuit for Reference Data



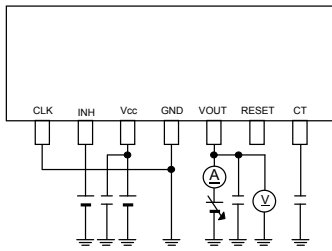
Measurement Circuit of Fig.1



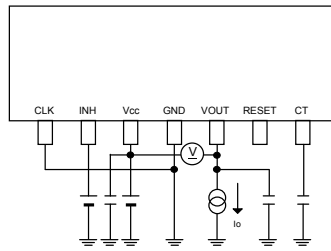
Measurement Circuit of Fig.2



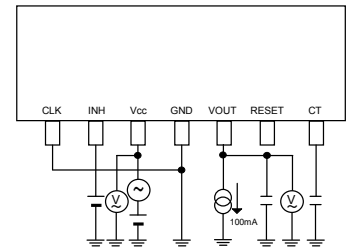
Measurement Circuit of Fig.3 and Fig.7 and Fig.8



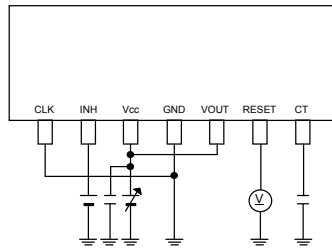
Measurement Circuit of Fig.4



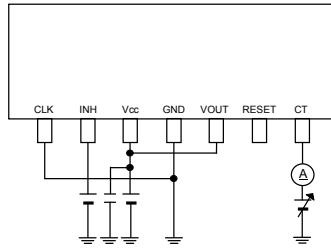
Measurement Circuit of Fig.5



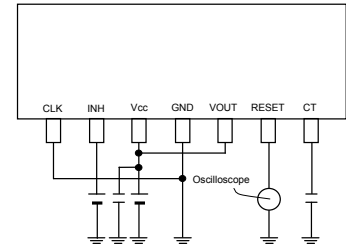
Measurement Circuit of Fig.6



Measurement Circuit of Fig.9 and Fig.11



Measurement Circuit of Fig.10



Measurement Circuit of Fig.12

●Block diagrams

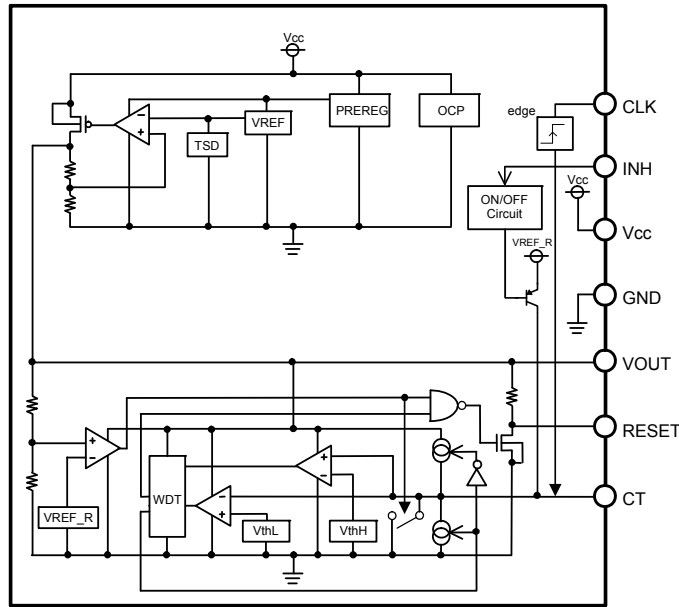
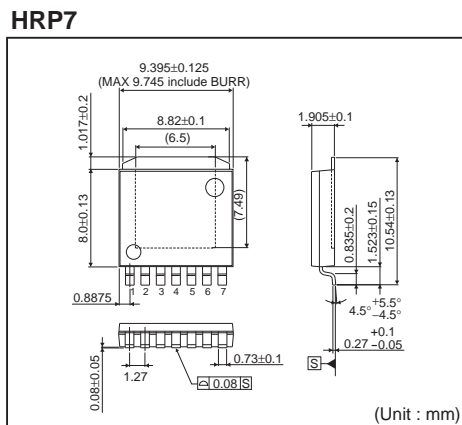


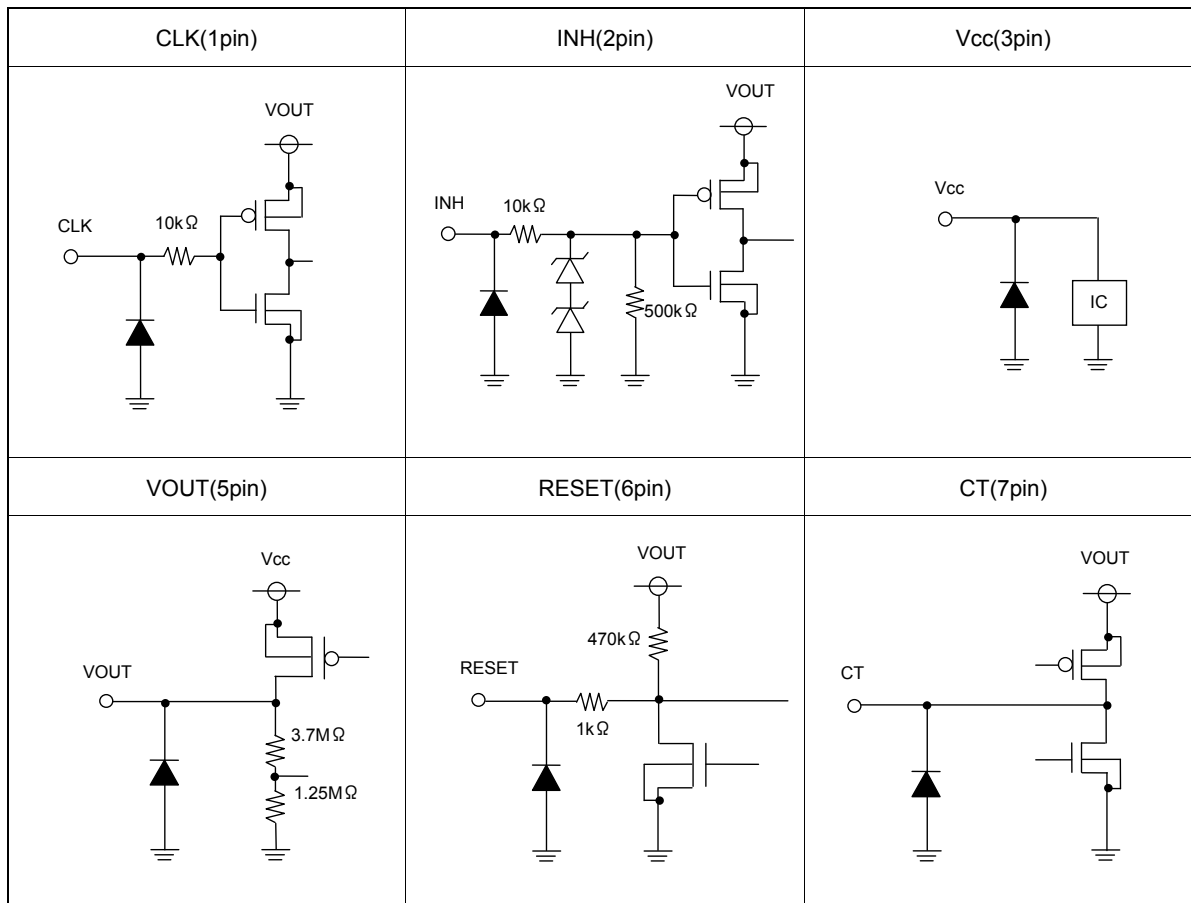
Fig.13

| Pin No. | Pin Name | Function |
|---------|----------|---|
| 1 | CLK | Clock Input from Microcontroller |
| 2 | INH | WDT ON/OFF Function Pin |
| 3 | Vcc | Power Supply Pin |
| 4 | GND | GND |
| 5 | VOUT | Voltage Output Pin |
| 6 | RESET | Reset Output Pin |
| 7 | CT | External Capacitance for Reset Output Delay Time, WDT Monitor Time Setting Connection Pin |
| Fin | GND | GND |

●TOP VIEW (Package dimension)



● Input / Output Equivalent Circuit Diagrams (Resistance value is typical value)



●BD3021HFP-M (Power on Reset / Watchdog Timer)

Power ON reset (output delay time) is adjustable by CT pin capacitor.

$$T_{dLH}(S) \approx (1.15V \times CT \text{ capacitance}(\mu F) / I_{ctc}(\mu A)) \text{ (Typ.)}$$

- T_{dLH} :Output delay time(power ON reset)
- 1.15V :Upper switching threshold voltage(Typ.)
- CT capacitance :capacitor connected to CT pin
- I_{ctc} :WDT charge current

Calculation example) with 0.01μF CT pin capacitor

$$T_{dLH}(S) = 1.15V \times 0.01\mu F / 6\mu A$$

$$\approx 1.9\text{msec}$$

※If the CT capacitance is not the same as the condition on the electrical characteristics table, i.e., 0.01μF, choose the capacitance value in ratio referring to the above equation.

Watch Dog Timer (WDT watch time, reset time) is adjustable by the CT pin capacitor

$$T_{WH}(S) \approx (1.00V \times CT \text{ capacitance} (\mu F)) / I_{ctd}(\mu A) \text{ (Typ.)}$$

$$T_{WL}(S) \approx (1.00V \times CT \text{ capacitance} (\mu F)) / I_{ctc}(\mu A) \text{ (Typ.)}$$

- T_{WH} :WDT watch time (delay time to turn the reset ON)
- T_{WL} :WDT reset time (time the reset is ON)
- 1.00V :Upper switching threshold voltage – lower switching threshold voltage
- CT capacitance :CT pin capacitor ※Shared with power ON reset
- I_{ctc} :WDT charge current
- I_{ctd} :WDT discharge current

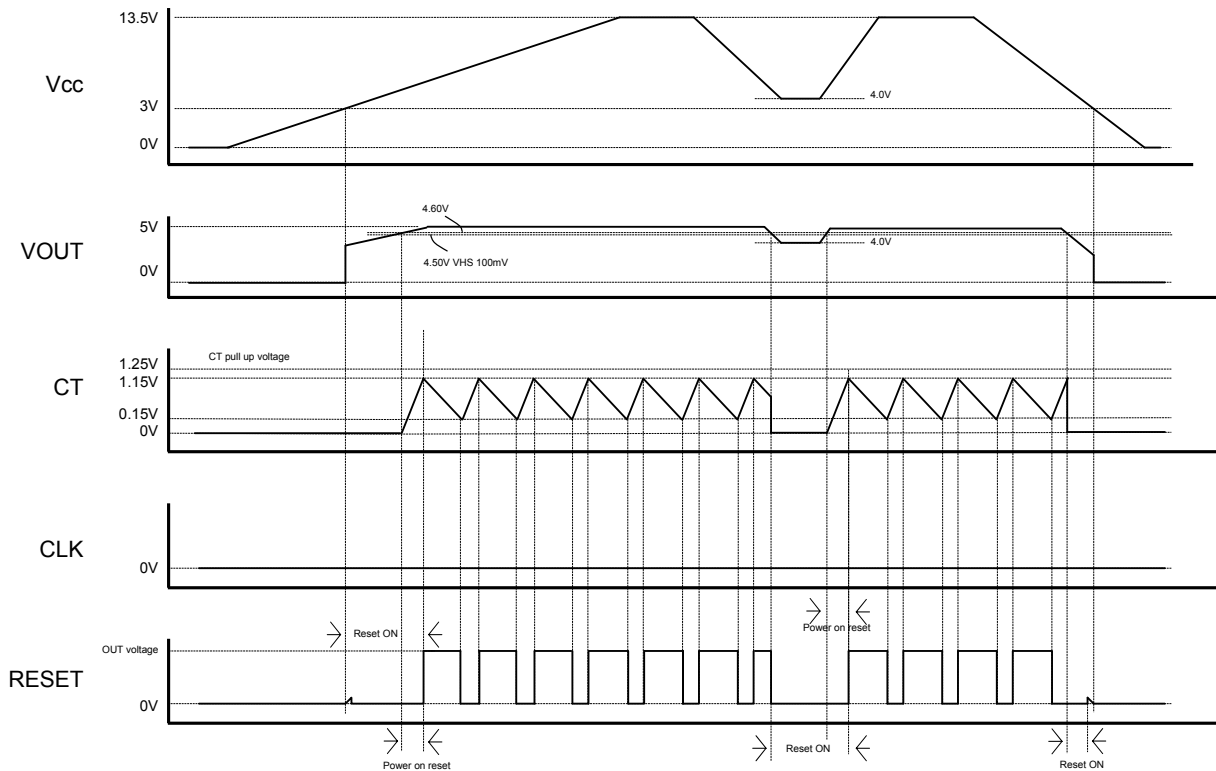
Calculation example) with 0.01μF CT pin capacitor

$$T_{WH}(S) \approx 1.00V \times 0.01\mu F / 2\mu A \approx 5.0\text{msec} \text{ (Typ.)}$$

$$T_{WL}(S) \approx 1.00V \times 0.01\mu F / 6\mu A \approx 1.7\text{msec} \text{ (Typ.)}$$

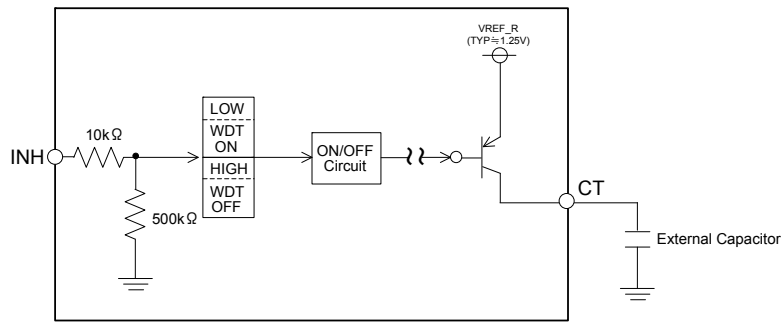
※If the CT capacitance is not the same as the condition on the electrical characteristics table, i.e., 0.01μF, choose the capacitance value in ratio referring to the above equation.

<Timing Chart>



●WDT timer ON/OFF switch INH (Resistance value is typical value)

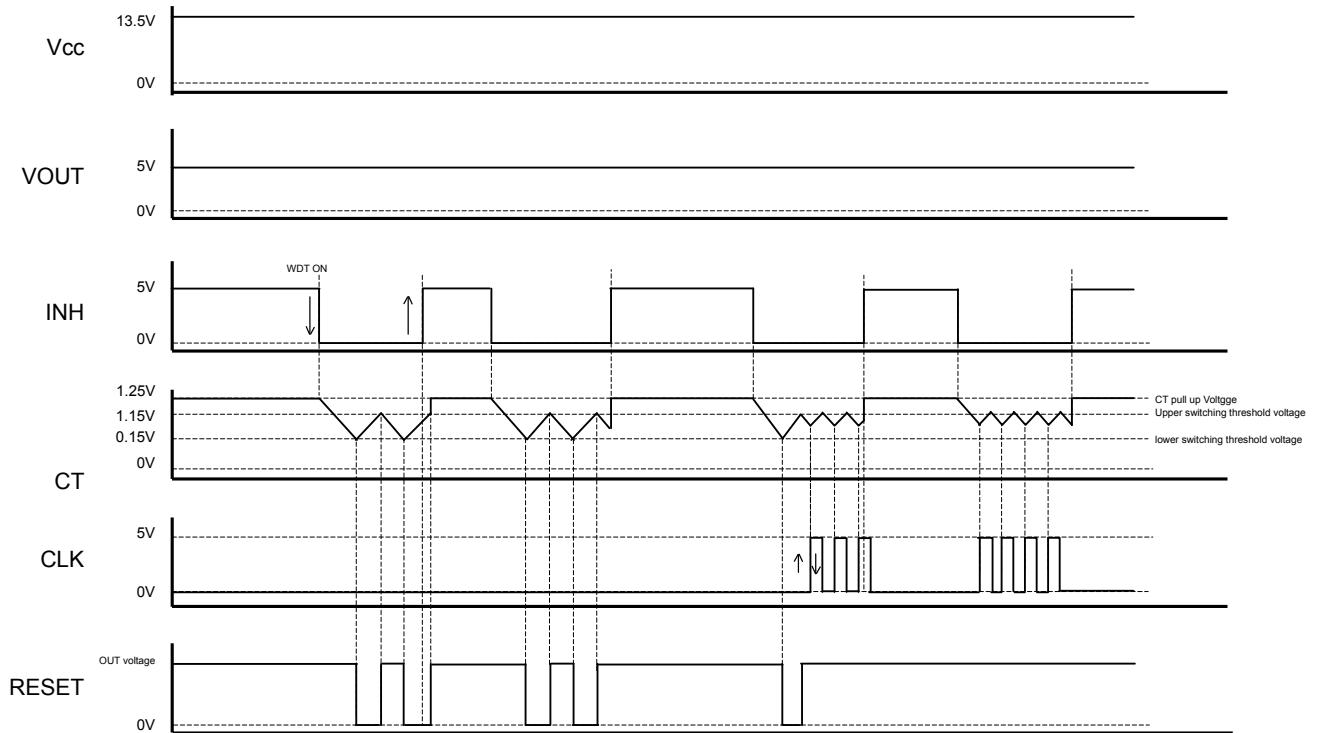
BD3021HFP-M has a switch INH to turn the WDT ON/OFF



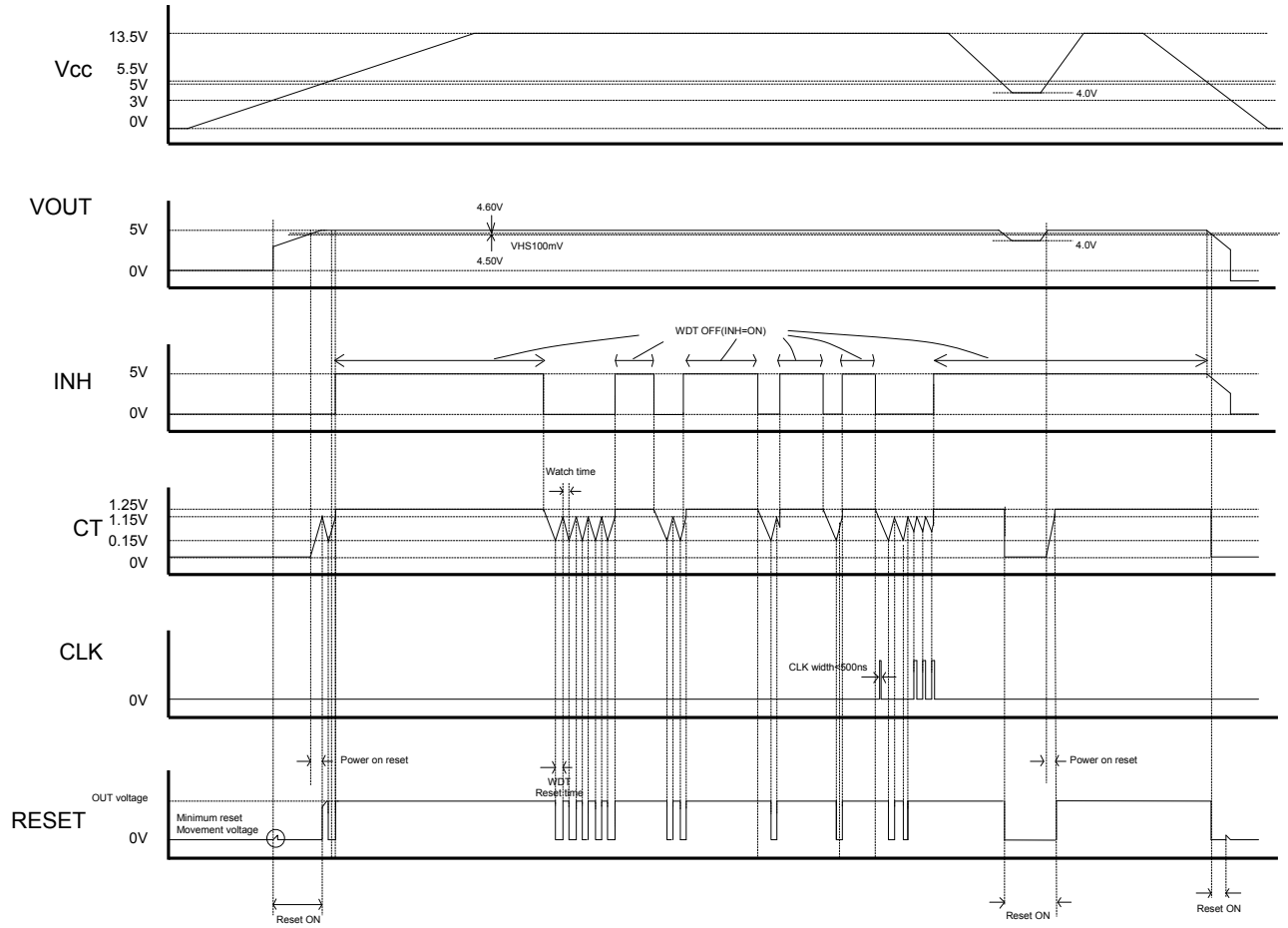
IC Internal Block Diagram

By using INH ON, CT potential can be pulled up to internal voltage VREF_R (invalid with power ON reset))

<Timing Chart>



<Timing Chart>



● Thermal Design

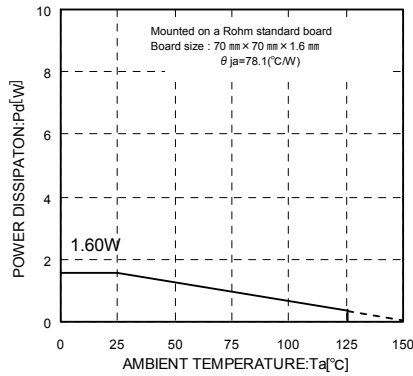


Fig. 14

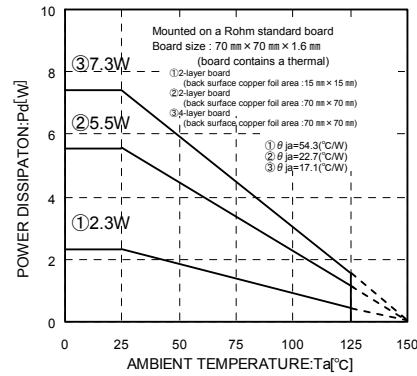


Fig. 15

Refer to Fig.14 and Fig.15 thermal dissipation characteristics for usage above $T_a=25^{\circ}\text{C}$. The IC's characteristics are affected heavily by the temperature, and if it exceeds its max junction temperature (T_{jmax}), the chip may degrade or destruct. Thermal design is critical in terms of avoiding Instantaneous destruction and reliability in long term usage. The IC needs to be operated below its max junction temperature (T_{jmax}) to avoid thermal destruction. Refer to Fig.14 and Fig.15 for HRP7 package thermal dissipation characteristics. Operate the IC within power dissipation (Pd) when using this IC. Power consumption P_c (W) calculation will be as below (for Fig.15③)

$$P_c = (V_{cc} - V_{OUT}) \times I_o + V_{cc} \times I_{cc2}$$

Power dissipation $P_d \geq P_c$

V_{cc} : Input Voltage
 V_{OUT} : Output Voltage
 I_o : Load Current
 I_{cc2} : Circuit Current

If load current I_o is calculated to operate within power dissipation, it will be as below, where you can find the max load current I_{oMax} for the applied voltage V_{cc} of the thermal design.

$$I_o \leq \frac{P_d - V_{cc} \times I_{cc2}}{V_{cc} - V_{OUT}} \quad (\text{Refer to Fig2 for } I_{cc2})$$

Example) at $T_a=125^{\circ}\text{C}, V_{cc}=12\text{V}, V_{OUT}=5\text{V}$

$$I_o \leq \frac{1.46 - 12 \times I_{cc2}}{12 - 5} \quad \left(\begin{array}{l} \text{Fig.15③ : } \theta_{ja}=17.1^{\circ}\text{C/W} \rightarrow -58.4\text{mW/}^{\circ}\text{C} \\ 25^{\circ}\text{C}=7.3\text{W} \rightarrow 125^{\circ}\text{C}=1.46\text{W} \end{array} \right)$$

$$I_o \leq 208\text{mA} \quad (I_{cc2}=150\mu\text{A})$$

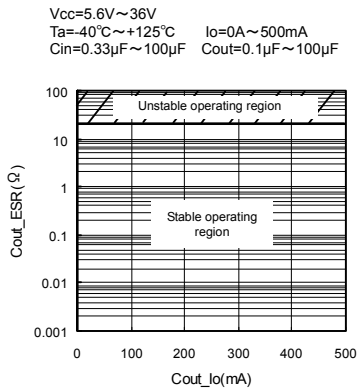
Refer to above and adjust the thermal design so it will be within power dissipation within the entire operation temperature range. Below is the power consumption P_c calculation when (V_{OUT} -GND short)

$$P_c = V_{cc} \times (I_{cc2} + I_{short}) \quad I_{short}: \text{short current}$$

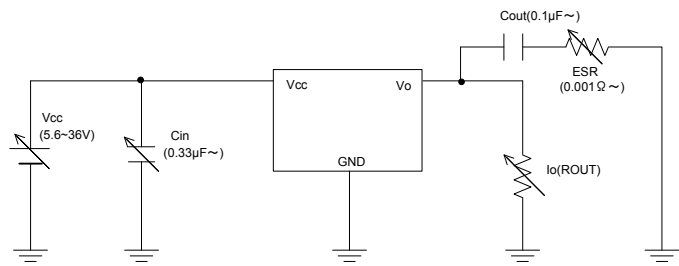
(Refer to Fig.4 for I_{short})

●Pin Settings / Precautions

1. Vcc Pin
Insert a 0.33 ~ 1000μF capacitor between the Vcc and GND pins. The appropriate capacitance value varies by application. Be sure to allow a sufficient margin for input voltage levels.
2. Output pins
It is necessary to place capacitors between each output pin and GND to prevent oscillation on the output. Usable capacitance values range from 0.1μF ~ 1000μF. Abrupt fluctuations in input voltage and load conditions may affect the output voltage. Output capacitance values should be determined only through sufficient testing of the actual application.



ESR vs Io(reference data)



※Pin Settings / Precautions 2 Measurement circuit

3. CT pin
Connecting a capacitance of 0.01μF ~ 1μF on the CT pin is recommended.

●Notes for use

1. Absolute maximum ratings
Use of the IC in excess of absolute maximum ratings (such as the input voltage or operating temperature range) may result in damage to the IC. Assumptions should not be made regarding the state of the IC (e.g., short mode or open mode) when such damage is suffered. If operational values are expected to exceed the maximum ratings for the device, consider adding protective circuitry (such as fuses) to eliminate the risk of damaging the IC.
2. Electrical characteristics described in these specifications may vary, depending on temperature, supply voltage, external circuits and other conditions. Therefore, be sure to check all relevant factors, including transient characteristics.
3. GND potential
The potential of the GND pin must be the minimum potential in the system in all operating conditions. Ensure that no pins are at a voltage below the GND at any time, regardless of transient characteristics.
4. Ground wiring pattern
When using both small-signal and large-current GND traces, the two ground traces should be routed separately but connected to a single ground potential within the application in order to avoid variations in the small-signal ground caused by large currents. Also ensure that the GND traces of external components do not cause variations on GND voltage. The power supply and ground lines must be as short and thick as possible to reduce line impedance.
5. Inter-pin shorts and mounting errors
Use caution when orienting and positioning the IC for mounting on printed circuit boards. Improper mounting may result in damage to the IC. Shorts between output pins or between output pins and the power supply or GND pins (caused by poor soldering or foreign objects) may result in damage to the IC.
6. Operation in strong electromagnetic fields
Using this product in strong electromagnetic fields may cause IC malfunction. Caution should be exercised in applications where strong electromagnetic fields may be present.
7. Testing on application boards
When testing the IC on an application board, connecting a capacitor directly to a low-impedance pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from a jig or fixture during the evaluation process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.
8. Thermal consideration
Use a thermal design that allows for a sufficient margin in light of the Pd in actual operating conditions. Consider Pc that does not exceed Pd in actual operating conditions. ($P_d \geq P_c$)

$$\left(\begin{array}{l} T_{jmax} : \text{Maximum junction temperature}=150^{\circ}\text{C}, T_a : \text{Peripheral temperature}[^{\circ}\text{C}], \\ \theta_{ja} : \text{Thermal resistance of package-ambience}[^{\circ}\text{C}/\text{W}], P_d : \text{Package Power dissipation [W]}, \\ P_c : \text{Power dissipation [W]}, V_{cc} : \text{Input Voltage}, V_{OUT} : \text{Output Voltage}, I_o : \text{Load}, I_{cc2} : \text{Bias Current2} \end{array} \right)$$

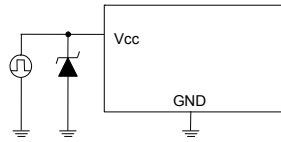
$$\text{Package Power dissipation} : P_d (\text{W}) = (T_{jmax} - T_a) / \theta_{ja}$$

$$\text{Power dissipation} : P_c (\text{W}) = (V_{cc} - V_{OUT}) \times I_o + V_{cc} \times I_{cc2}$$

9. Over current protection circuit (OCP)
The IC incorporates an integrated over-current protection circuit that operates in accordance with the rated output capacity. This circuit serves to protect the IC from damage when the load becomes shorted. It is also designed to limit output current (without latching) in the event of a large and instantaneous current flow from a large capacitor or other component. These protection circuits are effective in preventing damage due to sudden and unexpected accidents. However, the IC should not be used in applications characterized by the continuous or transitive operation of the protection circuits.
10. Thermal shutdown circuit (TSD)
The IC incorporates a built-in thermal shutdown circuit, which is designed to turn the IC off completely in the event of thermal overload. It is not designed to protect the IC from damage or guarantee its operation. ICs should not be used after this function has activated, or in applications where the operation of this circuit is assumed.
11. Applications or inspection processes where the potential of the Vcc pin or other pins may be reversed from their normal state may cause damage to the IC's internal circuitry or elements. Use an output pin capacitance of 1000μF or lower in case Vcc is shorted with the GND pin while the external capacitor is charged. Insert a diode in series with Vcc to prevent reverse current flow, or insert bypass diodes between Vcc and each pin.

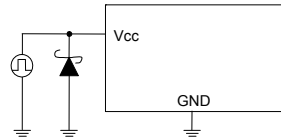
12. Positive voltage surges on VCC pin

A power zener diode should be inserted between VCC and GND for protection against voltage surges of more than 50V on the VCC pin.



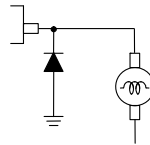
13. Negative voltage surges on VCC pin

A schottky barrier diode should be inserted between VCC and GND for protection against voltages lower than GND on the VCC pin.



14. Output protection diode

Loads with large inductance components may cause reverse current flow during startup or shutdown. In such cases, a protection diode should be inserted on the output to protect the IC.



15. Regarding input pins of the IC

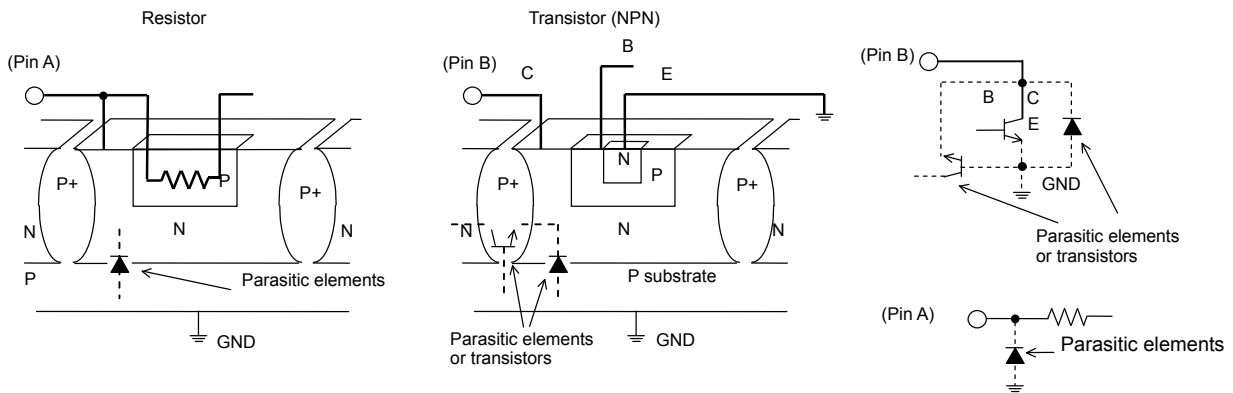
This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. PN junctions are formed at the intersection of these P layers with the N layers of other elements, creating parasitic diodes and/or transistors.

For example (refer to the figure below):

○When $GND > Pin A$ and $GND > Pin B$, the PN junction operates as a parasitic diode

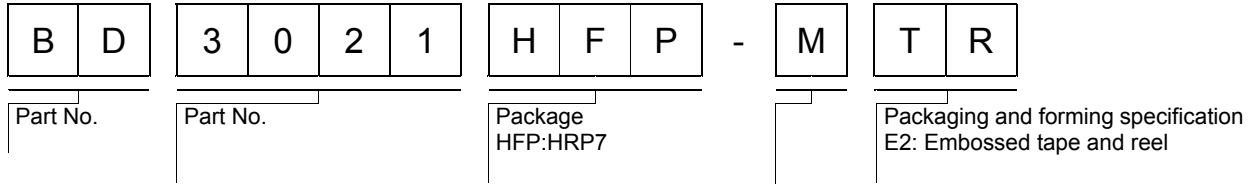
○When $GND > Pin B$, the PN junction operates as a parasitic transistor

Parasitic diodes occur inevitably in the structure of the IC, and the operation of these parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Accordingly, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.

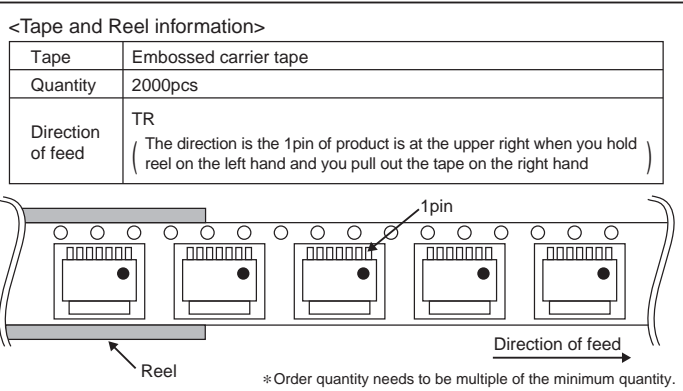
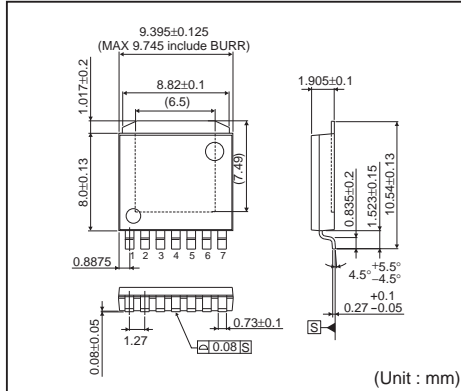


Example of Simple Monolithic IC Architecture

● Ordering part number



HRP7



Notes

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